

PN3568

NPN General Purpose Amplifier

• This device is designed for general purpose, medium power amplifiers and switches requiring collector currents to 500mA.



Absolute Maximum Ratings* T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.0	А
T _{J,} T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaird.

- These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics T_A =25°C unless otherwise noted

Parameter	Test Condition	Min.	Max.	Units
Off Characteristics				
Collector-Emitter Breakdown Voltage *	$I_C = 30 \text{mA}, I_B = 0$	60		V
Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_E = 0$	80		V
Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5.0		V
Collector Cut-off Current	$V_{CB} = 40V, I_E = 0$		50 5.0	nA μA
Emitter Cut-off Current	$V_{\text{CB}} = 4V, I_{\text{C}} = 0$ $V_{\text{EB}} = 4V, I_{\text{C}} = 0$		25	nΑ
cteristics				
DC Current Gain	$V_{CE} = 1.0V, I_{C} = 30mA$	40		
	$V_{CE} = 1.0V, I_{C} = 150mA$	40	120	
Collector-Emitter Saturation Voltage	I _C = 150mA, I _B = 15mA		0.25	V
Base-Emitter On Voltage	V _{CE} = 1.0V, I _C = 150mA		1.1	V
nal Characteristics	·		•	•
Output Capacitance	V _{CB} = 10V, f = 1.0MHz		20	pF
Input Capacitance	V _{EB} = 0.5V, f = 1.0MHz		80	
Small Signal Current Gain	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V}, f = 20 \text{MHz}$	3.0	30	
	Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current Cteristics DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage nal Characteristics Output Capacitance Input Capacitance	Collector-Emitter Breakdown Voltage * $I_C = 30$ mA, $I_B = 0$ Collector-Base Breakdown Voltage $I_C = 100\mu$ A, $I_C = 0$ Emitter-Base Breakdown Voltage $I_C = 10\mu$ A, $I_C = 0$ Collector Cut-off Current $I_C = 0$ Collector Cut-off Current $I_C = 0$ Emitter Cut-off Current $I_C = 0$ Emitter Cut-off Current $I_C = 0$ Current Gain $I_C = 0$ Current Gain $I_C = 0$ Collector-Emitter Saturation Voltage $I_C = 1.0$ V, $I_C = 30$ mA $I_C = 1.0$ V, $I_C = 1.0$ VA	Collector-Emitter Breakdown Voltage * $I_C = 30$ mA, $I_B = 0$ 60 Collector-Base Breakdown Voltage $I_C = 100$ µA, $I_C = 0$ 80 Emitter-Base Breakdown Voltage $I_E = 10$ µA, $I_C = 0$ 5.0 Collector Cut-off Current $V_{CB} = 40$ V, $I_C = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 40$ V, $I_C = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 40$ V, $I_C = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 40$ V, $V_{CC} = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 40$ V, $V_{CC} = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 40$ V, $V_{CC} = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 40$ V, $V_{CC} = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 40$ V, $V_{CC} = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 40$ V, $V_{CC} = 0$ 7.0 Emitter Cut-off Current $V_{CB} = 1.0$ V, $V_{CC} =$	Collector-Emitter Breakdown Voltage * $I_C = 30$ mA, $I_B = 0$ 60 Collector-Base Breakdown Voltage $I_C = 100$ µA, $I_C = 0$ 80 Emitter-Base Breakdown Voltage $I_C = 100$ µA, $I_C = 0$ 5.0 Collector Cut-off Current $V_{CB} = 40$ V, $I_C = 0$ 5.0 Emitter Cut-off Current $V_{CB} = 40$ V, $I_C = 0$ 25 Emitter Cut-off Current $V_{CB} = 40$ V, $I_C = 0$ 25 Exteristics DC Current Gain $V_{CE} = 1.0$ V, $I_C = 30$ mA 40 40 Collector-Emitter Saturation Voltage $I_C = 150$ mA, $I_C = 150$ mA 40 120 Collector-Emitter On Voltage $V_{CE} = 1.0$ V, $I_C = 150$ mA 1.1 That Characteristics Output Capacitance $V_{CB} = 10$ V, $I_C = 1.0$ MHz 80

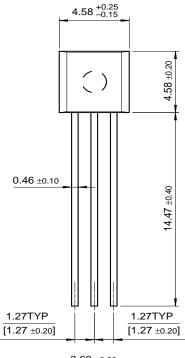
* Pulse Test: Pulse Width ≤ 300ms, Duty Cycle ≤ 2.0%

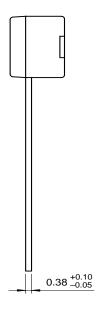
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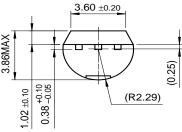
Thermal Characteristics T _A =25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

Package Dimensions

TO-92







Dimensions in Millimeters

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